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## **RFMD Ships Pre-Production Gallium Nitride (GaN)-Based CATV Hybrid Amplifiers to Major U.S.-Based CATV Equipment Provider**

### **RFMD's GaN Hybrid Amplifiers Provide Highest Available RF Output Levels for Cable Operators in Fiber Deep Network Architectures**

GREENSBORO, N.C., Dec 9, 2009 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, announced today that RFMD has commenced pre-production shipments of high-performance gallium nitride (GaN)-based CATV hybrid amplifiers to a major U.S.-based cable television (CATV) equipment provider.

Operators of hybrid fiber coax (HFC) networks are installing fiber capacity deeper into their networks ("fiber deep" networks) in order to address the increasing demand for higher throughput video and broadband services. Accordingly, CATV equipment providers looking to reduce the cost of fiber deep networks are seeking semiconductor devices capable of higher RF output levels than those available from today's state-of-the-art GaAs-based devices.

RFMD's GaN CATV hybrid amplifiers provide industry-leading RF output levels, and cable operators using RFMD's GaN can reduce the number of amplifiers required in emerging architectures, also known as N+1 architectures, and achieve up to 20-percent cost savings in fiber deep networks.

"We are excited to announce pre-production shipments of our GaN-based CATV hybrid amplifiers to this major CATV customer," said Alastair Upton, general manager of RFMD's Broadband Components business unit. "With our GaN semiconductor expertise and our world-class CATV manufacturing capability, RFMD is uniquely positioned to bring the next generation of high-performance CATV amplifiers to the CATV equipment market."

RFMD's initial GaN shipments to this CATV customer are intended for use in optical nodes, and subsequent shipments are also expected to be used in line extender amplifier applications. Volume production is expected in the first half of calendar 2010.

RFMD has a leading position in the design and production of high-performance CATV hybrid amplifiers and leads the industry in the application of GaN technology to the CATV market. RFMD is currently shipping GaN-based CATV hybrid amplifiers to CATV equipment suppliers in Europe, Japan and North America.

#### About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at [www.rfmd.com](http://www.rfmd.com).

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements,

other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, variability in operating results, the rate of growth and development of wireless markets, risks associated with the reduced investment in our wireless systems business, our ability to execute on our plans to consolidate or relocate manufacturing operations, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, dependence on gallium arsenide (GaAs) for the majority of our products, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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